

AMENDMENTS TO THE SPECIFICATION

- Please amend the paragraph beginning on page 7, line 9, as follows:

Around the first channel 202 is the first channel dielectric layer 208, which includes a region of barrier polymeric silicon carbide (SiC(H)) material 225, which is known to have good diffusion barrier properties, in the non-barrier SiCOH material and separating the SiCOH material from the first channel 202. The first channel 202 is made up of a first seed layer 228 around a first conductor core 230. The second channel 204 and the via 206 are surrounded by a second region of barrier SiC(H) material 231 in the non-barrier SiCOH material. The second channel 204 includes a second seed layer 234 around a second conductor core 236.